

Silicon PNP Power Transistor

2SB884

DESCRIPTION

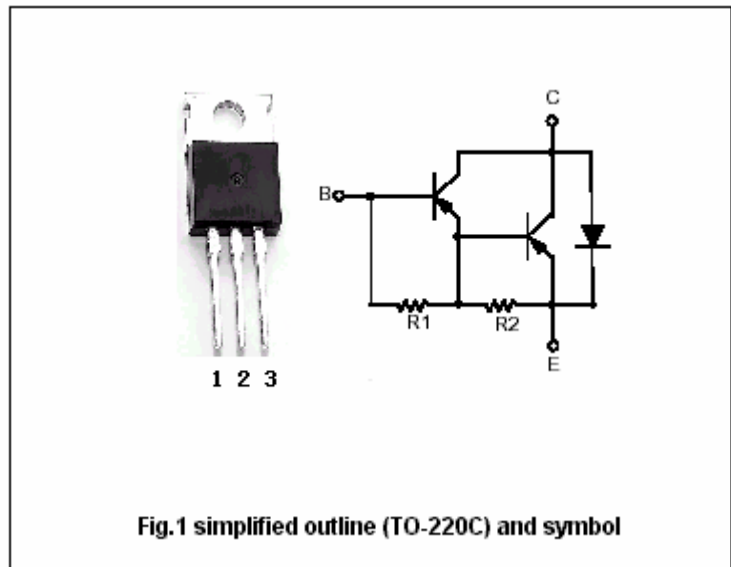
- With TO-220C package
- DARLINGTON
- High DC current gain
- Low collector saturation voltage
- Complement to type 2SD1194

APPLICATIONS

- For motor drivers,printer hammer drivers,relay drivers,voltage regulator control applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings($T_c=25^\circ$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-110	V
V_{CEO}	Collector-emitter voltage	Open base	-100	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current-DC		-3	A
I_{CM}	Collector current-Pulse		-5	A
P_C	Collector power dissipation	$T_c=25^\circ$	30	W
		$T_a=25^\circ$	1.75	
T_j	Junction temperature		150	$^\circ$
T_{stg}	Storage temperature		-55~150	$^\circ$

Silicon PNP Power Transistor

2SB884

CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-50mA, R _{BE} =∞	-100			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-5mA, I _E =0	-110			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-1.5A, I _B =-3mA		-1.0	-1.5	V
V _{BE sat}	Base-emitter saturation voltage	I _C =-1.5A, I _B =-3mA			-2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-80V, I _E =0			-0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-3.0	mA
h _{FE}	DC current gain	I _C =-1.5A; V _{CE} =-3V	1500			
f _T	Transition frequency	V _{CE} =-5V, I _C =-1.5A		20		MHz

Switching times

t _{on}	Turn-on time	I _C =-1A; V _{CC} =-50V I _{B1} =-I _{B2} =-2mA; R _L =50Ω		0.8		μs
t _{stg}	Storage time			2.4		μs
t _r	Turn-off time			1.2		μs

Silicon PNP Power Transistor

2SB884

PACKAGE OUTLINE

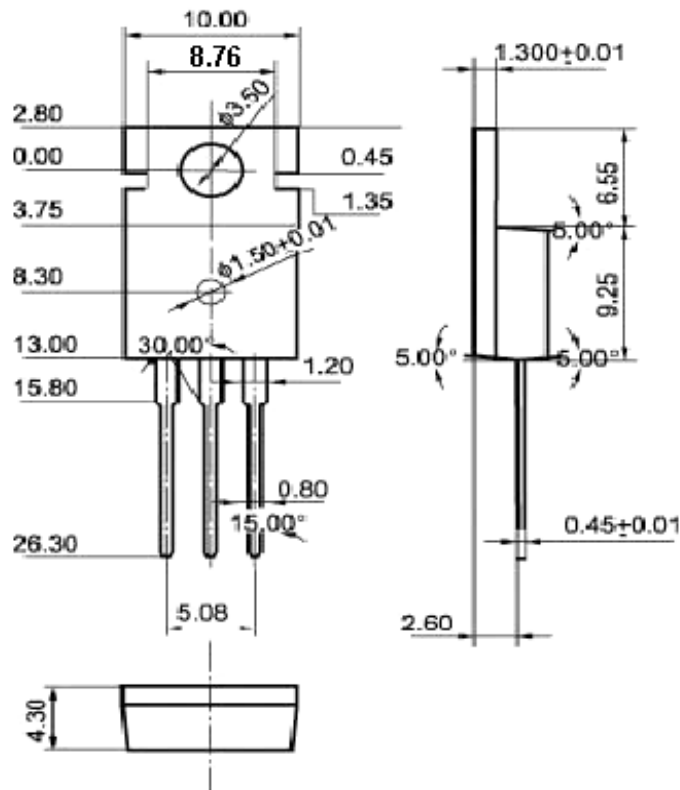


Fig.2 Outline dimensions